

ZTX560

E-LINE PNP SILICON PLANAR HIGH VOLTAGE TRANSISTOR

FEATURES

- Excellent h_{FE} characteristics up to $I_C=50mA$
- Low Saturation voltages

PARTMARKING

ZTX
560



E-LINE

ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	VALUE	UNIT
Collector-base voltage	V_{CBO}	-500	V
Collector-emitter voltage	V_{CEO}	-500	V
Emitter-base voltage	V_{EBO}	-5	V
Peak pulse current	I_{CM}	-500	mA
Continuous collector current	I_C	-150	mA
Power dissipation	P_{tot}	1	W
Operating and storage temperature range	$T_j:T_{stg}$	-55 to +150	°C

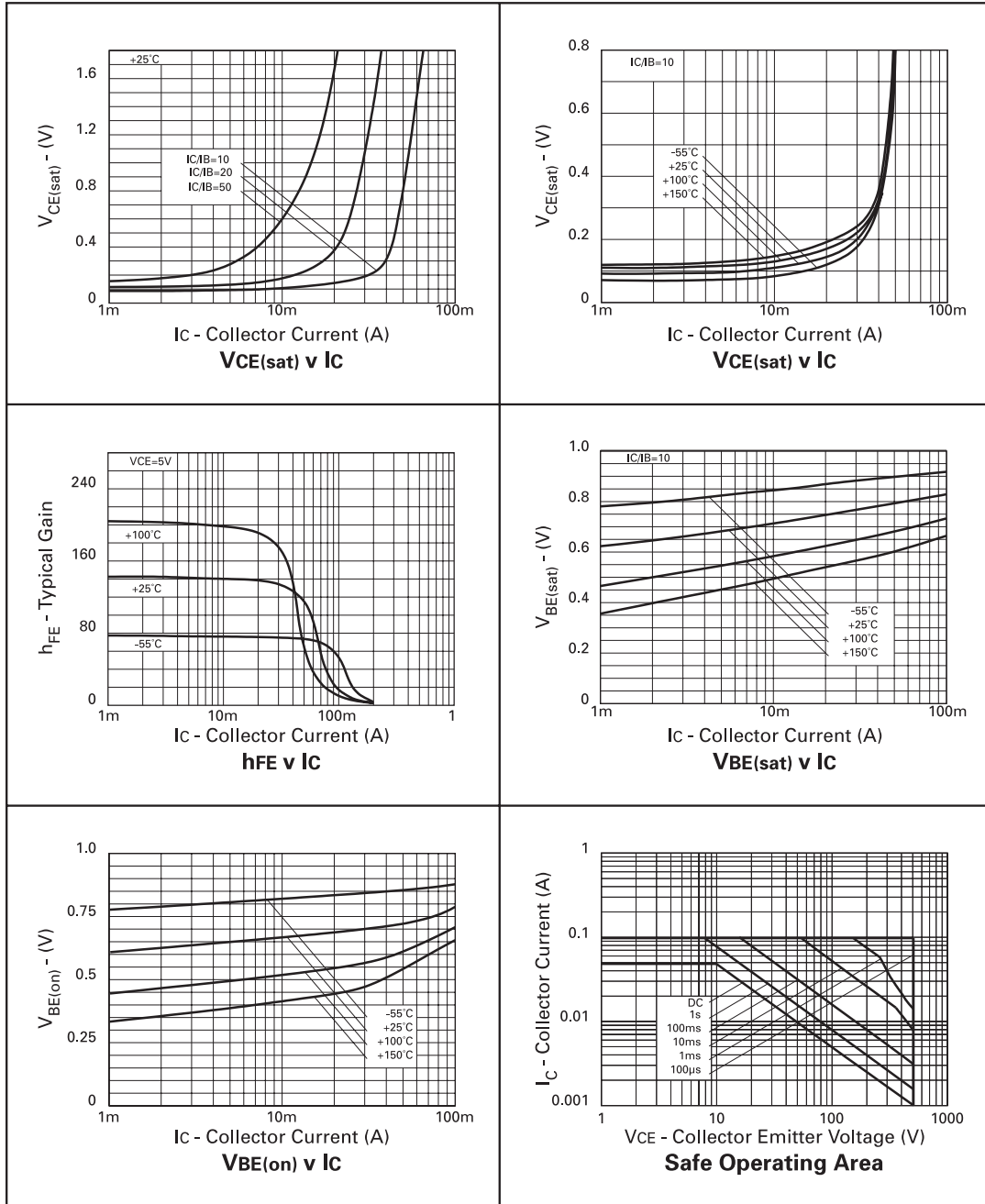
ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^\circ C$)

PARAMETER	SYMBOL	MIN.	MAX.	UNIT	CONDITIONS
Collector-base breakdown voltage	$V_{(BR)CBO}$	-500		V	$I_C = -100\mu A$
Collector-emitter breakdown voltage	$V_{BR(CEO)}$	-500		V	$I_C = -10mA^*$
Emitter-base breakdown voltage	$V_{(BR)EBO}$	-5		V	$I_E = -100\mu A$
Collector cut-off current	$I_{CBO}; I_{CES}$		-100	nA	$V_{CB} = -500V; V_{CE} = -500V$
Emitter cut-off current	I_{EBO}		-100	nA	$V_{EB} = -5V$
Collector-emitter saturation voltage	$V_{CE(sat)}$		-0.2 -0.5	V	$I_C = -20mA, I_B = -2mA^*$ $I_C = -50mA, I_B = -10mA^*$
Base-emitter saturation voltage	$V_{BE(sat)}$		-0.9	V	$I_C = -50mA, I_B = -10mA^*$
Base-emitter turn on voltage	$V_{BE(on)}$		-0.9	V	$I_C = -50mA, V_{CE} = -10V^*$
Static forward current transfer ratio	h_{FE}	100 80 15 typ	300 300		$I_C = -1mA, V_{CE} = -10V$ $I_C = -50mA, V_{CE} = -10V^*$ $I_C = -100mA, V_{CE} = -10V^*$
Transition frequency	f_T	60		MHz	$V_{CE} = -20V, I_C = -10mA,$ $f = 50MHz$
Output capacitance	C_{obo}		8	pF	$V_{CB} = -20V, f = 1MHz$
Switching times	t_{on} t_{off}	110 typ. 1.5 typ.		ns μs	$V_{CE} = -100V, I_C = -50mA,$ $I_{B1} = -5mA, I_{B2} = 10mA$

* Measured under pulsed conditions. Pulse width=300 μs . Duty cycle $\leq 2\%$

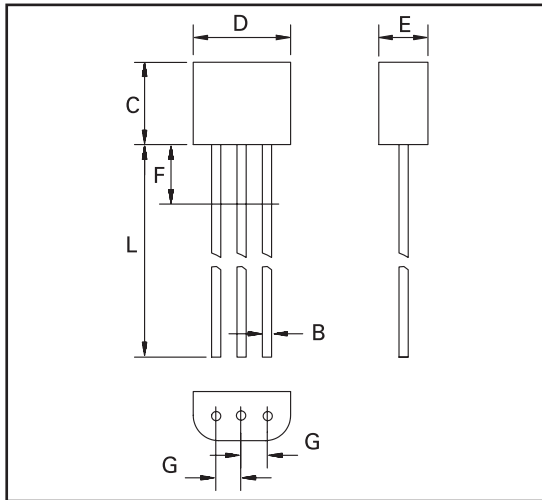
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TYPICAL CHARACTERISTICS



ZTX560

PACKAGE OUTLINE



PACKAGE DIMENSIONS

DIM	Millimeters		Inches	
	Min	Max	Min	Max
A	0.41	0.495	0.016	0.0195
B	0.41	0.495	0.016	0.0195
C	3.61	4.01	0.142	0.158
D	4.37	4.77	0.172	0.188
E	2.16	2.41	0.085	0.095
F	—	2.50	—	0.098
G	1.27 NOM		0.050 NOM	
L	13.00	13.97	0.512	0.550

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